

# The Roaring 20s - A Renaissance for the Semiconductor Industry



**Todd Younkin**

SRC, President and CEO

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# Special Thanks

- William Chen, ASE
- Bill Bottoms, 3MTS
- Ravi Mahajan, Intel

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- Choong-Un Kim, UT/Arlington
- Ganesh Subbarayan, Purdue
- Carol Handwerker, Purdue
- Amy Marconnet, Purdue
- Justin Weibel, Purdue
- Bahgat Sammakia, SUNY-Binghamton
- Muhannad Bakir, Georgia Tech
- Madhavan Swaminathan, Georgia Tech
- Timothy Fisher, UCLA
- Arijit Raychowdhury, Georgia Tech

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- *Other CHIRP Center Faculty*
- *Matthew Johnston, Oregon State*
- *Subramanian Iyer, UCLA*

+ Their amazing  
partners and  
students

*Insufficient Time  
to Share More*

# BLUF

- The Heterogeneous Integration Roadmap (HIR) is both a **critical reference** and **an innovation community**.
- Academic research related to HIR is crucial, with fruitful areas in both basic & applied research. This includes all 23 HIR chapters, plus growing vectors like quantum, additive manufacturing, & biology.
- SRC has significantly grown its long-standing commitment to heterogeneous integration or advanced packaging at universities worldwide. For example, GRC-PKG has grown **+867% over last 5 years**.
- Academics should familiarize themselves with **SRC's "3 Pillars"** (or 3 Ps), and then...
- Academics should **submit proposals** to these three solicitations (First two are active, Third is planned):

Program	Eligible Performers	Announced	Link
JUMP 2.0	U.S. (DARPA)	Dec. 21, 2021	<a href="https://www.darpa.mil/news-events/2021-12-22">https://www.darpa.mil/news-events/2021-12-22</a>
NSF REU Program*	U.S. (NSF)	Jan. 26, 2022	<a href="https://www.nsf.gov/news/news_summ.jsp?cntn_id=304304&amp;org=ENG&amp;from=news">https://www.nsf.gov/news/news_summ.jsp?cntn_id=304304&amp;org=ENG&amp;from=news</a>
GRC, Packaging (PKG)	U.S. & International	Q2, 2022	<a href="https://www.src.org/compete/">https://www.src.org/compete/</a>

- SRC is pursuing CHIPS ACT funding to revitalize and modernize our mission, aligned to the 3 Ps. **Heterogeneous integration is priority #1** for SRC and its members.

\*Administered by NSF. Do not work with SRC or SRC member companies as it is a conflict of interest.

# The Future of Semiconductors Is Bright

- I started at Intel in 2001, excited about nanotechnology and Intel's race to the atomic length scale. **It did not disappoint.**
- Recently, the talent pipeline has started to dry up, significantly. The student population is not receptive to the "2D scaling forever" story. **That narrative is not finding a way into their hearts and minds!**
- Together, we must seek a new narrative. One that helps students realize we have **hard yet interesting problems that can't be solved without them.**
- All can see the \$2T+ **generational opportunities** in hyperscaled computing, artificial intelligence, 5/6G+, autonomous vehicles, and quantum. We know these emerging frontiers will change the world around us!
- Yet, collectively, we must apply disciplined imagination. Microelectronics is not static! The future we imagine rests on continued, cost-effective, and innovative **breakthroughs in hardware.** Materials, integration, packaging, design, architecture, and security are all critical elements for success.



There is a bright future. Fascinating opportunities for the next 20 - 30 years, the kind you can build a career on as a young scientist or engineer.

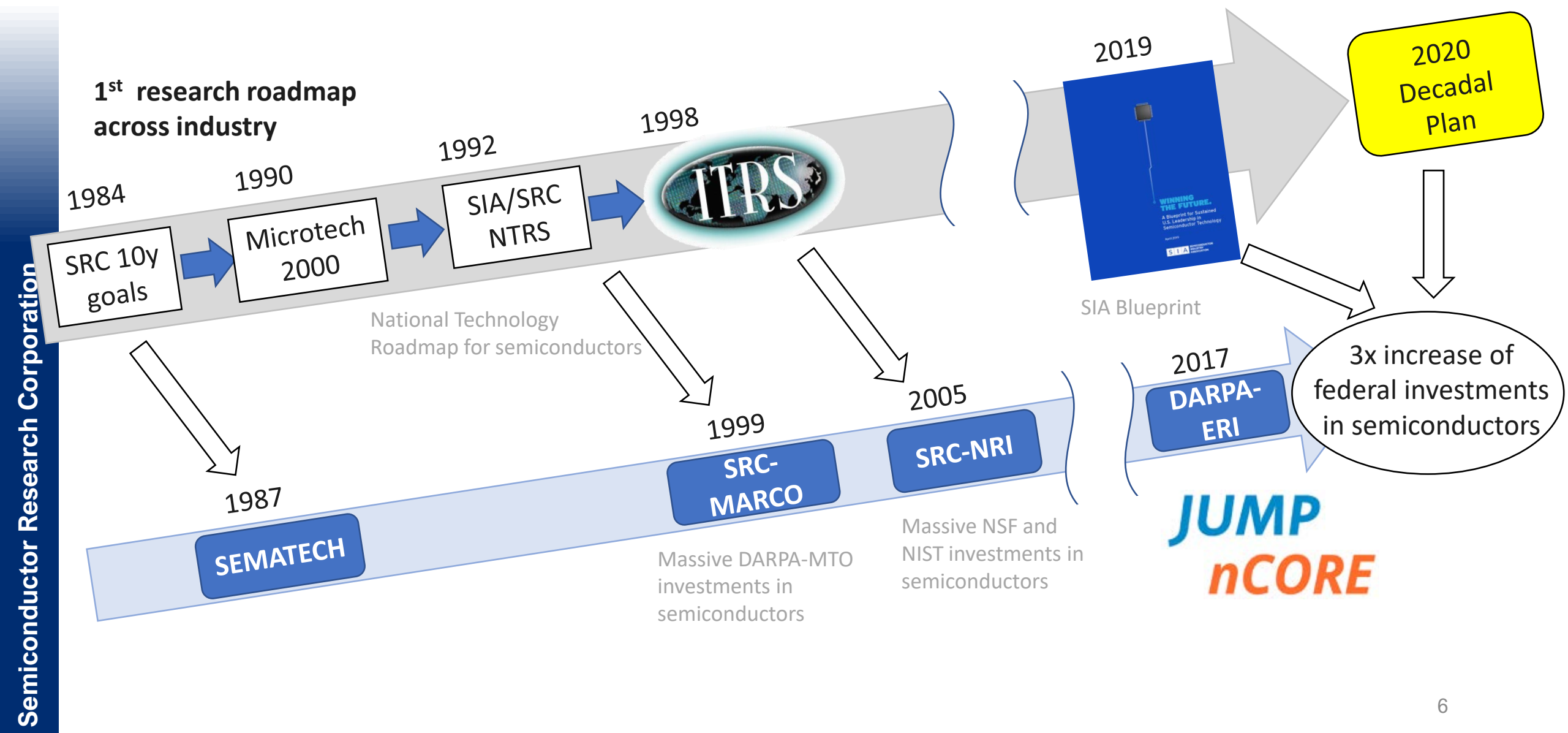
# Premier Microelectronics Consortium Since 1982

Private Sector and Interagency, Participation and Governance



SRC is a neutral, trusted advisor that serves a vast network of engineers. All are dedicated to research, prototyping, and workforce training programs in advanced semiconductor technologies

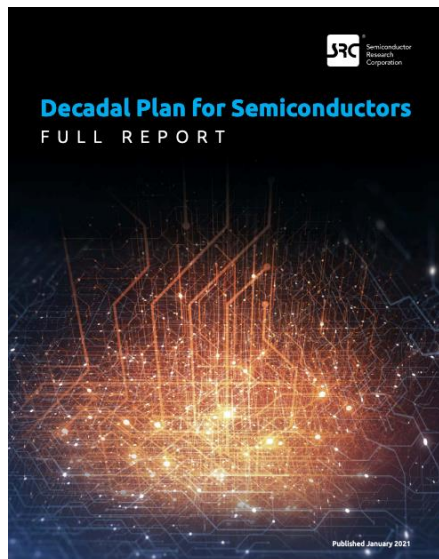
# Thought Leadership That Positions Our Industry





# The “3 Ps” - SRC’s Guiding Principles This Decade

## Prosperity



**Jan 2021**

Published Full  
2030 Decadal Plan for  
Semiconductors

**5 Seismic Shifts, ICT Drivers  
Call w/ SIA for ↑ Annual Funding**

[www.src.org/about/decadal-plan/](http://www.src.org/about/decadal-plan/)

## The People



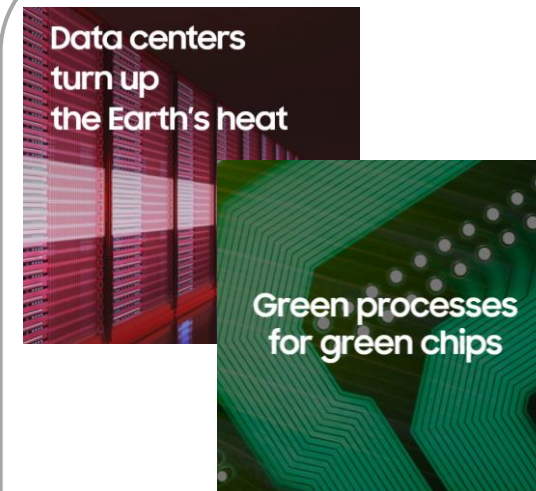
**Apr 2021**

Released SRC’s Broadening  
Participation Pledge

**Student Pipeline (AA,BS,MS,PhD)  
Greater Diversity, Equity, &  
Inclusion  
Ignite passion in US Citizens**

[www.src.org/about/broadening-participation/](http://www.src.org/about/broadening-participation/)

## The Planet



*Images from Samsung*

**Oct 2021**

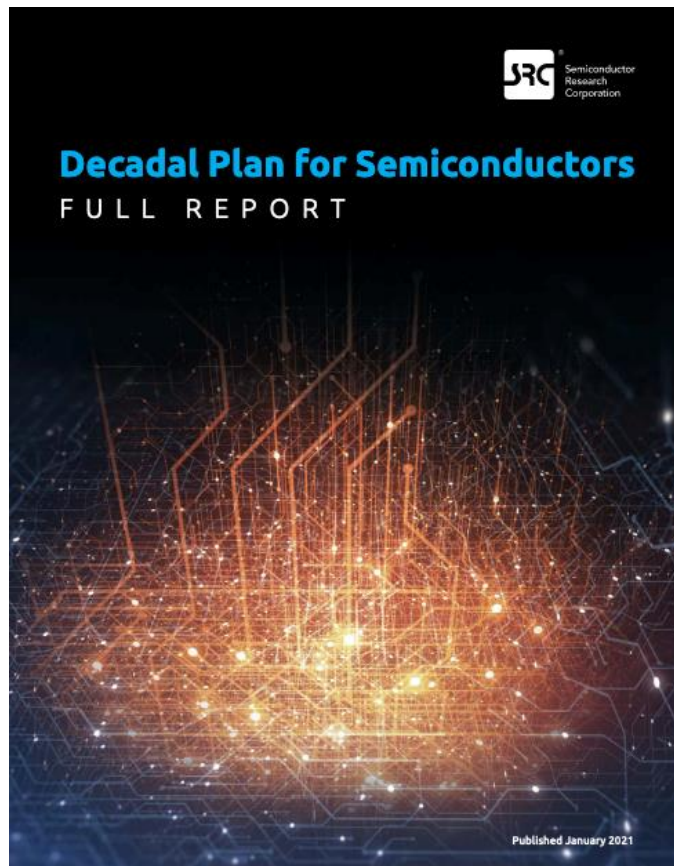
Released SRC’s  
Commitment to Sustainability

**Green Materials & Processes  
Energy Efficient ICT Systems**

<https://www.src.org/about/sustainability/>

**Nov' 20 - Announced *\$3.4 Billion Plan* Aims to Stimulate US Semiconductor R&D**

<https://www.allaboutcircuits.com/news/newly-announced-3point4-billion-plan-aims-stimulate-us-semiconductor-rd/>



<https://www.src.org/about/decadal-plan/>

## Five “Seismic Shift” Research Priorities



Smart  
Sensing

**The Analog Data Deluge**



Memory  
& Storage

**The Growth of Memory and Storage Demands**



Communication

**Communication Capacity vs. Data Generation**



Security

**ICT Security Challenges**



Energy  
Efficiency

**Compute Energy vs. Global Energy Production**



# Heterogeneous Integration Roadmap

## Technical Working Groups

### HI Market Applications

- High Performance Computing & Data Center
- Mobile
- Medical, Health & Wearables
- Automotive
- IoT
- Aerospace & Defense

### Heterogeneous Integration Components

- Single Chip and Multi Chip Integration (including Substrates)
- Integrated Photonics
- Integrated Power Electronics
- MEMS & Sensor integration
- 5G & Beyond - RF and Analog Mixed Signal

### Cross Cutting topics

- Materials & Emerging Research Materials
- Emerging Research Devices
- Test
- Supply Chain
- Security
- Thermal Management
- Reliability

### Integration Processes

- SiP
- 3D +2D & Interconnect
- WLP (fan in and fan out)

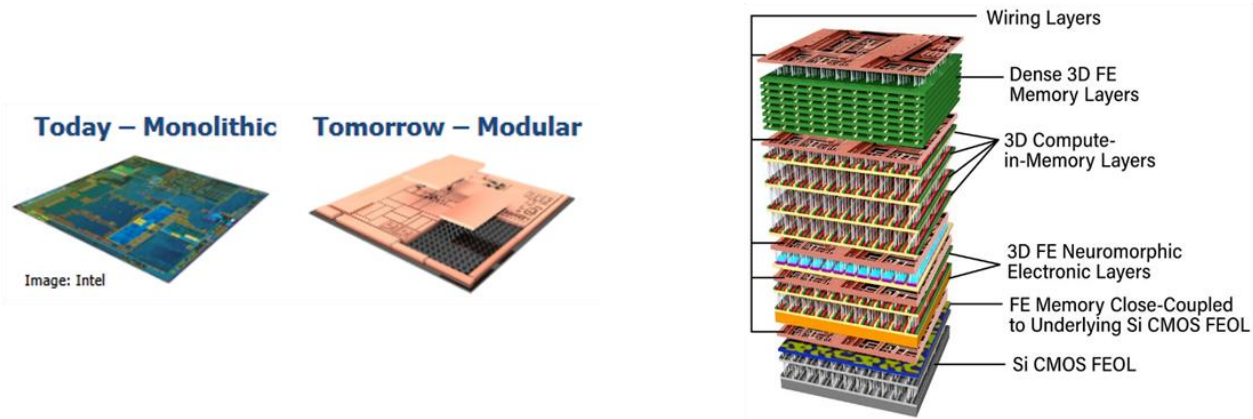
### Design

- Co-Design
- Modeling & Simulation



# Microelectronics & Advanced Packaging Technologies (MAPT)

*We must evaluate market-driven opportunities “side-by-side” to realize lasting innovations*



**Priority 1**

## 2.5D and 3D Advanced Packaging

Image: DARPA/Intel  
<https://www.darpa.mil/program/common-heterogeneous-integration-and-ip-reuse-strategies>

**Priority 2**

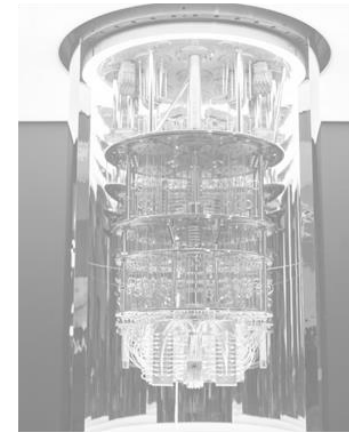
## 3D Super Chips

Image: SIRO, Penn State, Prof. Vijay Narayanan  
<https://news.psu.edu/story/625834/2020/07/15/research/over-10-million-awarded-penn-state-energy-center>

**Priority 3**

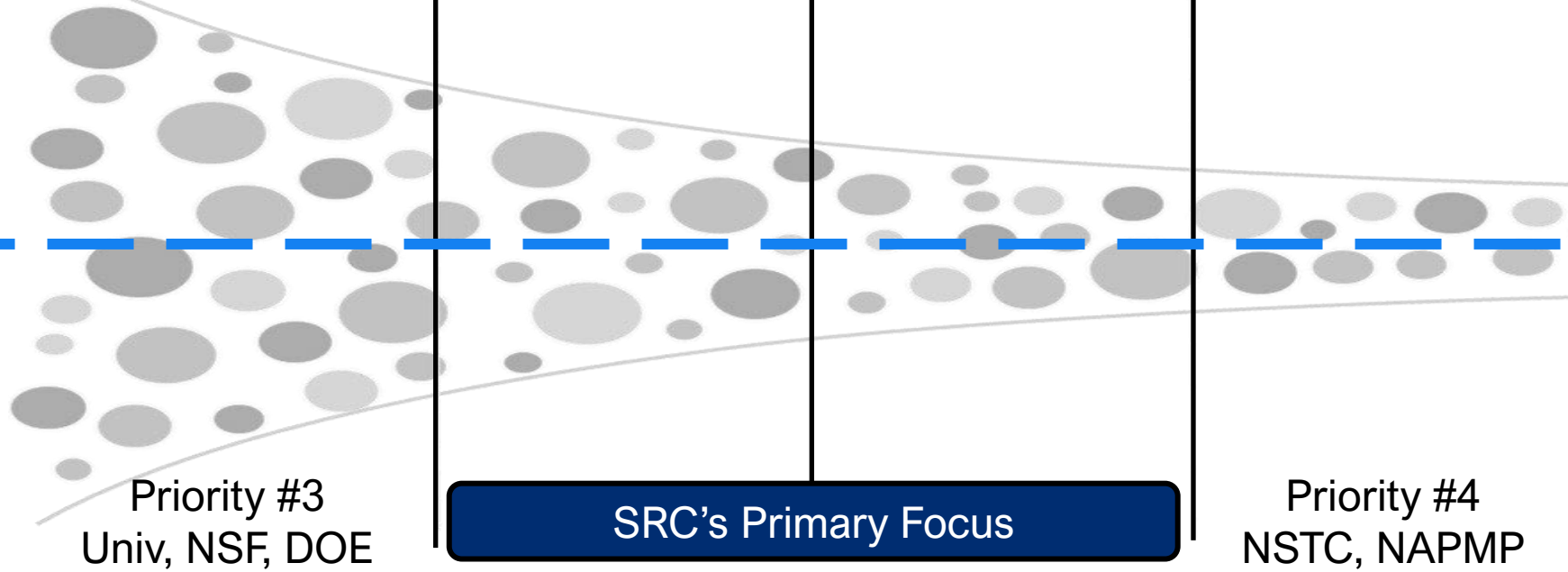
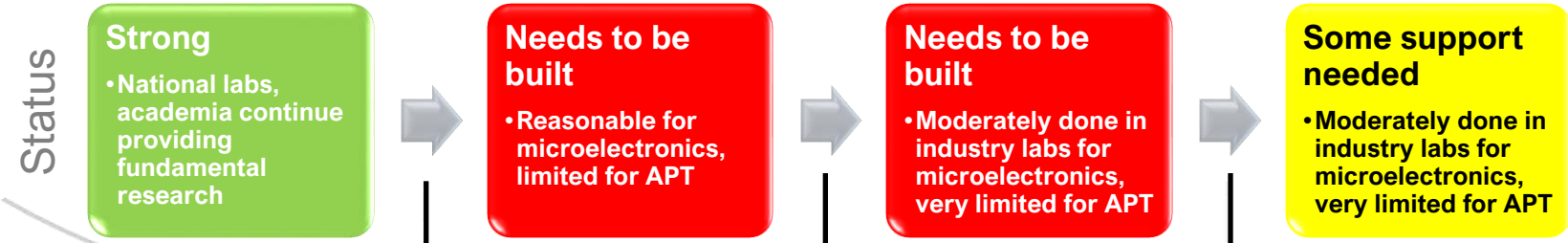
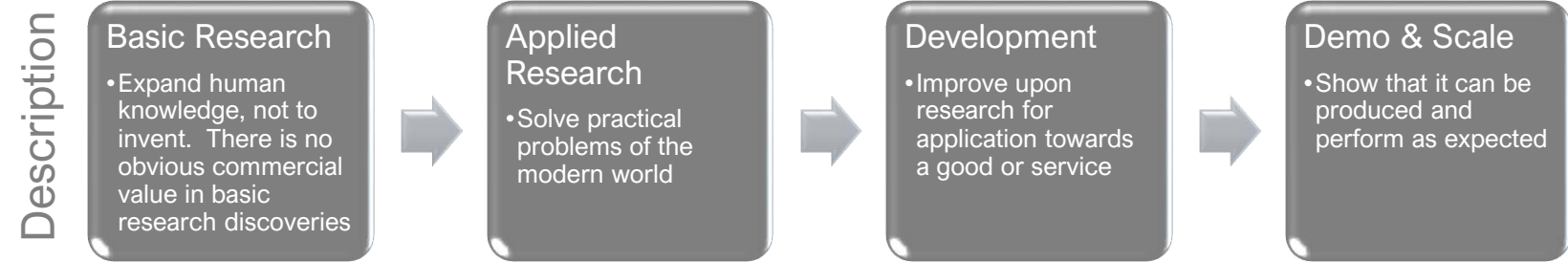
## Hardware for New Paradigms

Image: IBM Q system displayed at CES 2020  
<https://www.fiercееlectronics.com/electronics/what-quantum-computing>



We need a Lab-to-Fab approach to MAPT Innovation. A robust pipeline from start to finish.  
**SRC's 2030 Decadal Plan for Semiconductors is the “What” and the HIR is some of the “How.”**

Complete  
Vision



USG Funding

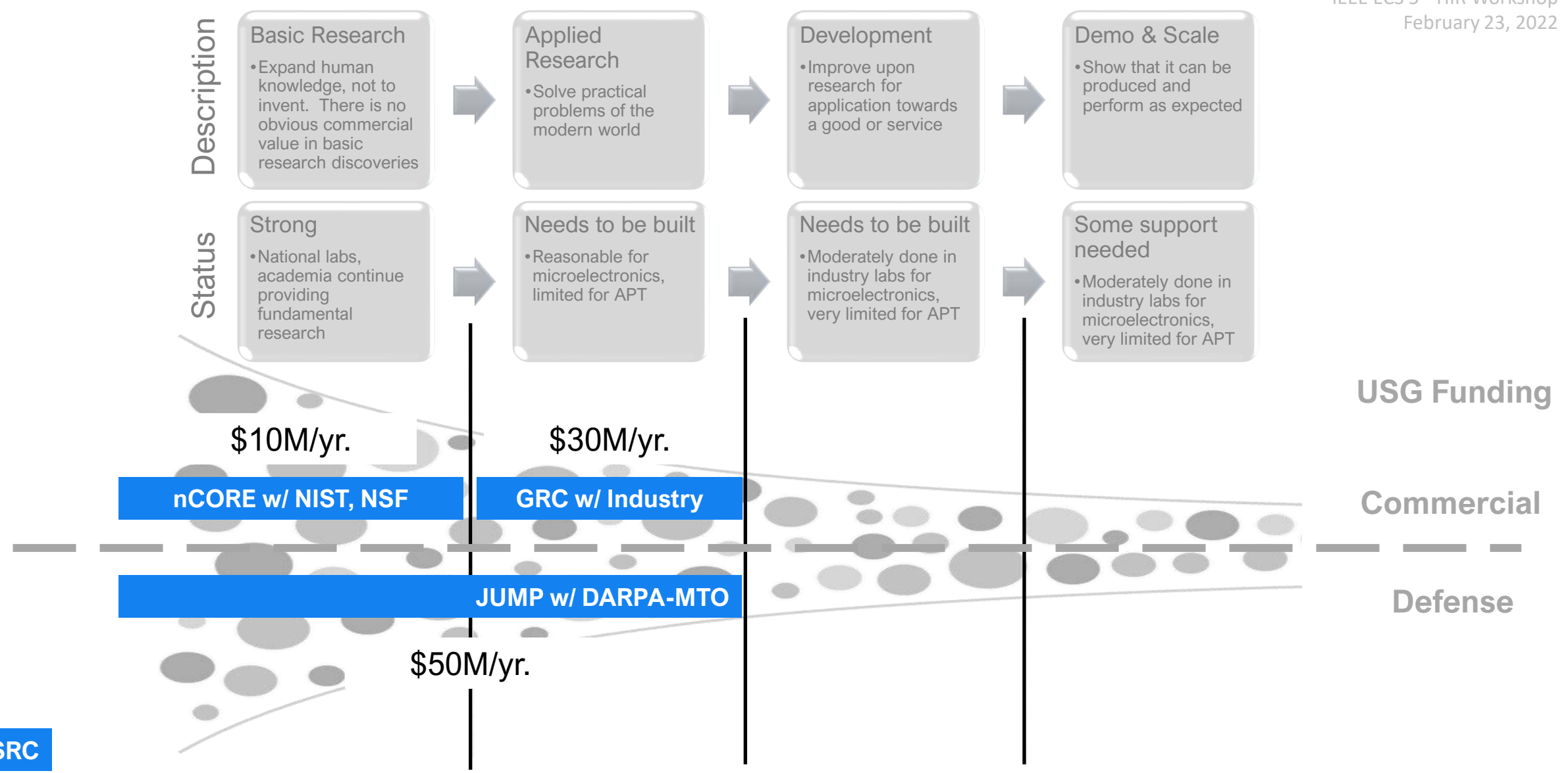
Commercial

Defense

Priority #3  
Univ, NSF, DOE

SRC's Primary Focus

Priority #4  
NSTC, NAPMP



## GRC w/ Industry

## PKG

UT/Arlington

33 Research Projects  
15 Universities  
**53 SRC Scholars**  
37 Faculty Researchers  
73 Liaison Personnel

## CHIRP Center\*



Ganesh Subbarayan



Bahgat Sammakia

13 Research Projects  
2 Universities  
**29 SRC Scholars**  
15 Faculty Researchers  
32 Liaison Personnel

## JUMP w/ DARPA

## ASCENT

Dir. Suman Datta  
(Notre Dame)AD Sayeef Salahuddin  
(UCB)

63 Research Projects  
16 Universities  
**133 SRC Scholars**  
42 Faculty Researchers  
209 Liaison Personnel

## ComSenTer

Dir. Mark Rodwell  
(UCSB)AD Ali Niknejad  
(UCB)

39 Research Projects  
10 Universities  
**80 SRC Scholars**  
25 Faculty Researchers  
73 Liaison Personnel

\*CHIRP Center statistics are included in the overall GRC/PKG numbers



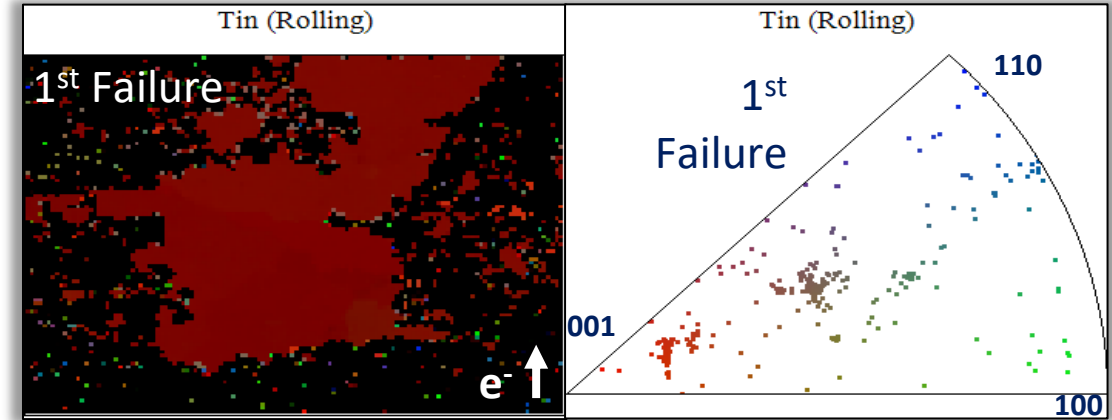
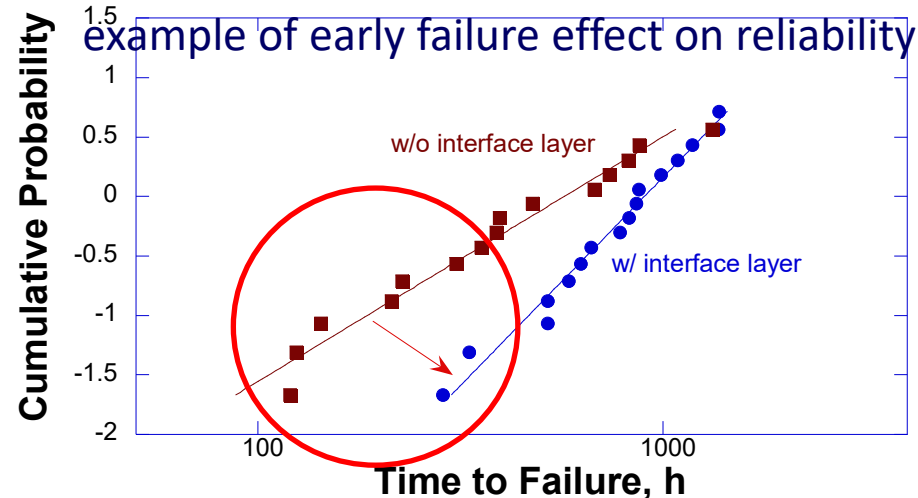
# Source of Early Failures and How to Suppress

## ■ Suppression of early failures

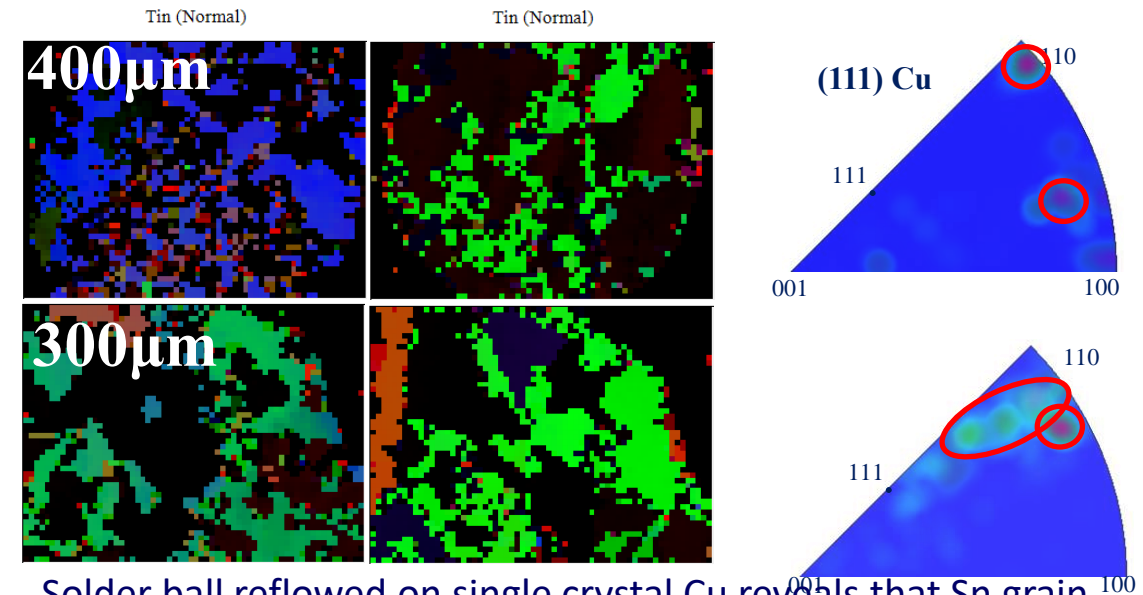
- may be most effective and practical in improving EM reliability
- our research finds that the early failures area always related to [001] Sn grain alignment to EM.

## ■ [001] Sn effect can be suppressed by

- using Cu substrate with controlled orientation (our study w/ Cu single crystal proven that Sn grain orientation is biased by Cu orientation)
- fine grain structure (but may not be practical)



EBSD characterization of EM failed samples reveals that early failed joint is with [001] Sn grain alignment.



Solder ball reflowed on single crystal Cu reveals that Sn grain formation is biased. The bias effect is more in smaller solder.

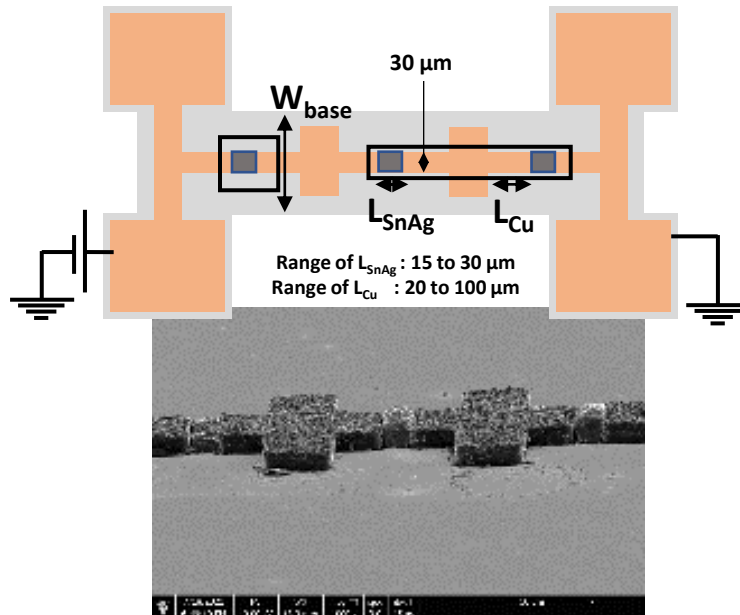


# Characterization of Sub-30 $\mu\text{m}$ Pitch $\mu$ -Bumps for Next Generation 2.5D Packages

Ganesh Subbarayan and Carol Handwerker, Purdue University

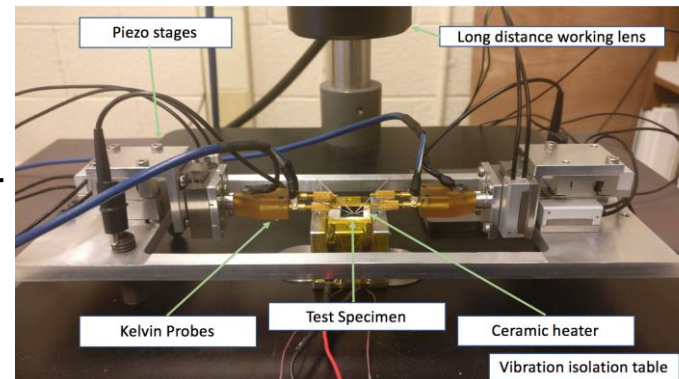
## Goals

- Electromigration characterization of sub-30  $\mu\text{m}$  pitch solder  $\mu$ -bumps
- Characterization of electromigration influenced intermetallic growth and phase segregation

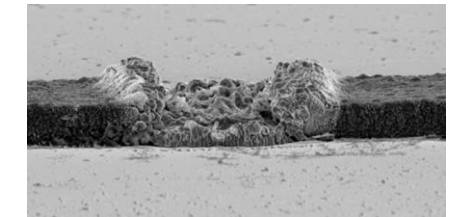
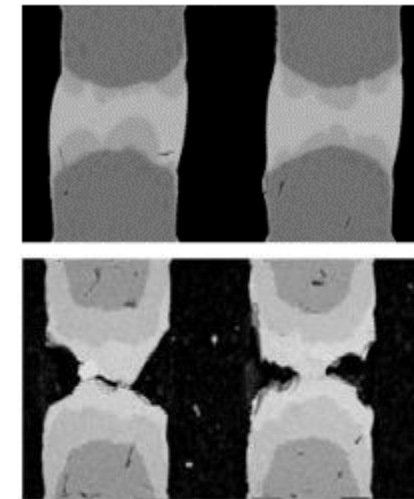


## Significant Results

- Designed and fabricated test device for testing sub-30  $\mu\text{m}$  solder joints
- Developed electromigration test setup for use *in-situ* or *ex-situ*
- Simulated solder voiding using phase field models



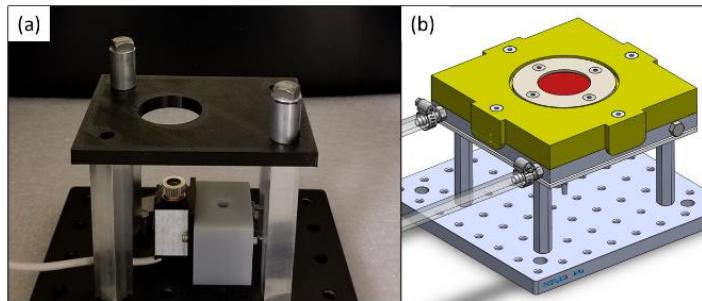
Nano-Resolution Probe Experimental Setup



**Task Objective:** Develop, validate, and demonstrate a standardized, versatile, robust method for characterizing low thermal contact resistance interfaces ( $<0.01^\circ\text{C}\cdot\text{cm}^2/\text{W}$ ) applicable to a variety of different packaging applications

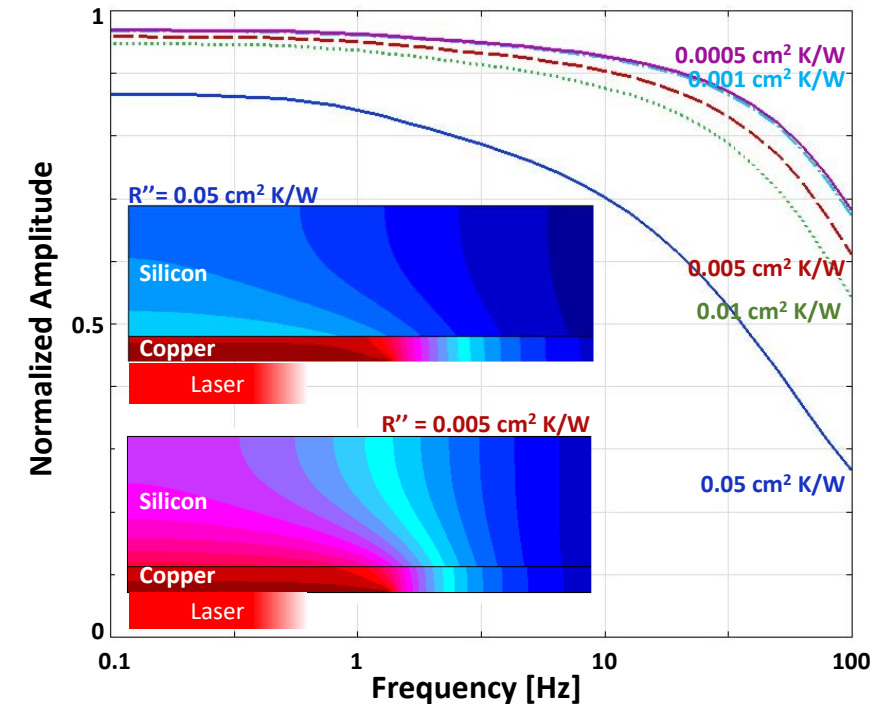
**Approach and Goals:**

- (1) Develop and optimize the experimental test fixture based on target applications
- (2) Construct the test fixture and validate the measurement based on benchmark interfaces that can be quantified with standard methods



Prototype test fixture for the radial Angstrom method using single layers samples that forms a starting point for developing the metrology technique for this task.

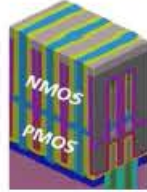
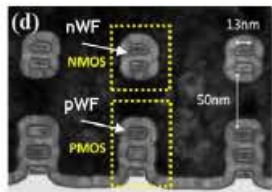
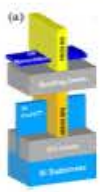
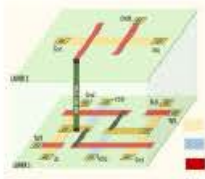

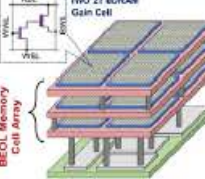
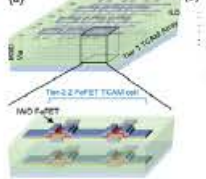
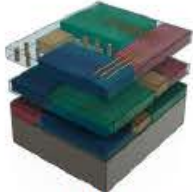

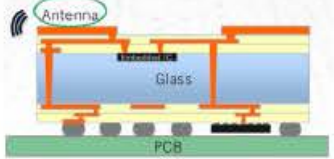
- (3) Demonstrate the low interface resistance measurement capability on application-relevant samples identified by the liaisons.
- (4) Develop analytical or hybrid (analytical + finite element) models to determine the thermal resistances for a multilayer stack as a function of the temperature evolution and (separately determined) material properties without measurement of absolute temperatures.



Preliminary COMSOL results for the temperature oscillation amplitude (at the top of the silicon layer) as a function of frequency and contact resistance for a Si-Cu interface. Insets show the amplitude as a function of position within the multilayer structure for two selected interfacial resistances.

# Monolithic, Polyolithic and Heterogenous 3D Integration

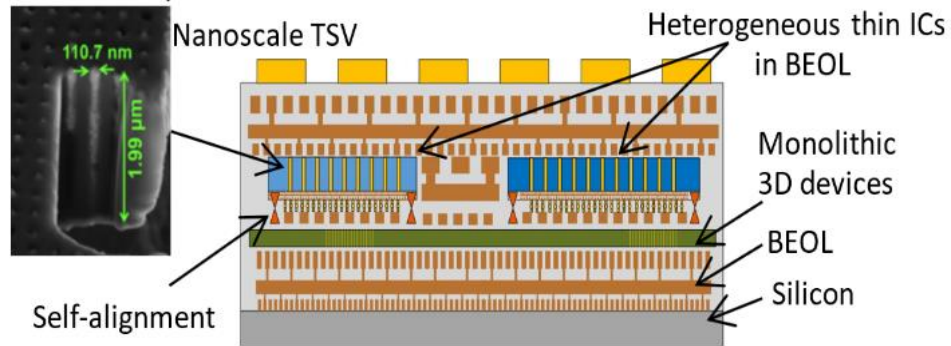
Scaling  
Heterogenous integration

Category	Granularity	Technology	Interconnect Density ( $\text{mm}^{-2}$ )	Examples
3D Transistor (before M1)	Transistor	<ul style="list-style-type: none"> <li>Epitaxial growth                             <ul style="list-style-type: none"> <li>Stacked nanosheet</li> </ul> </li> <li>Sequential Integration                             <ul style="list-style-type: none"> <li><i>in situ</i> dep and anneal</li> <li>layer transfer &amp; bonding</li> </ul> </li> </ul>	$10^9$	 C-FET  Stacked Nanosheet  Ge nanosheet PMOS on FinFET NMOS
Monolithic 3D (after M1)	Gate, Block	<ul style="list-style-type: none"> <li>Sequential Integration                             <ul style="list-style-type: none"> <li><i>in situ</i> dep and anneal</li> <li>layer transfer &amp; bonding</li> </ul> </li> </ul>	$>10^8$	 3D Transpose SRAM  3D RRAM  3D eDRAM  3D FeFET TCAM
Polyolithic 3D (W2W bonding)	sBlock, Chiplet	<ul style="list-style-type: none"> <li>Parallel Integration                             <ul style="list-style-type: none"> <li>Hybrid bonding</li> <li>Metal ALD</li> </ul> </li> </ul>	$10^6 - 10^8$	 SiO <sub>2</sub> -reconstituted tier in the BEOL  CMOS Base-Band Chip
Heterogeneous 2.5/3D Integration	Chiplets, modules	<ul style="list-style-type: none"> <li>3D Packaging</li> </ul>	$10^4 - 10^5$	 Stacked and assembled chiplets on glass interposer

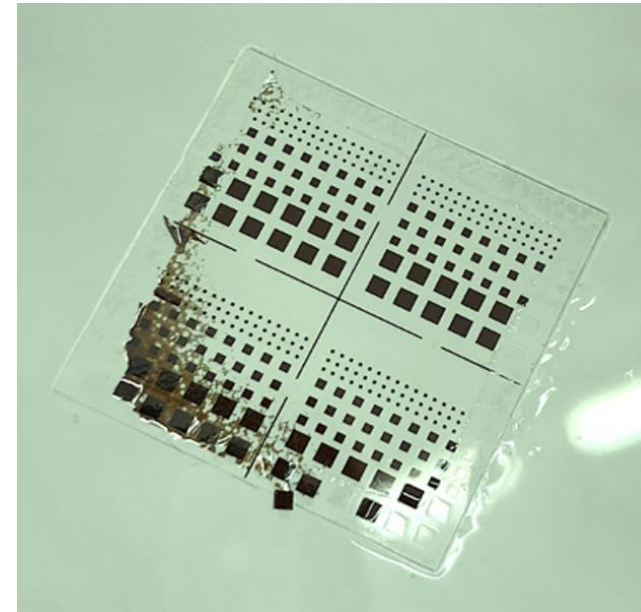


# Examples of Heterogeneous Integration Technologies from Georgia Tech's *Integrated 3D Systems Lab (i3DS)*

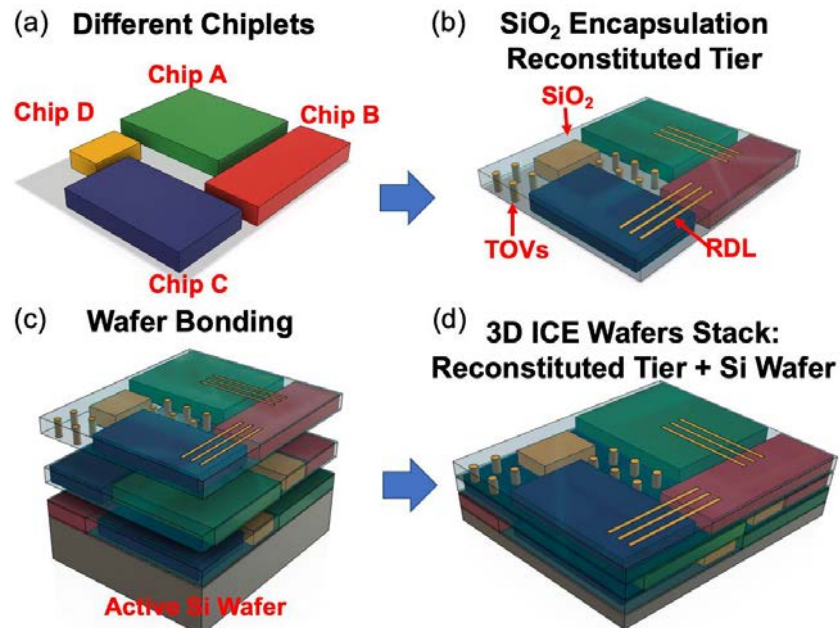
Pseudo-monolithic 3D: *heterogeneous* integration of device tier *within/near* the BEOL



SiO<sub>2</sub>-reconstituted-tier mounted on a glass wafer



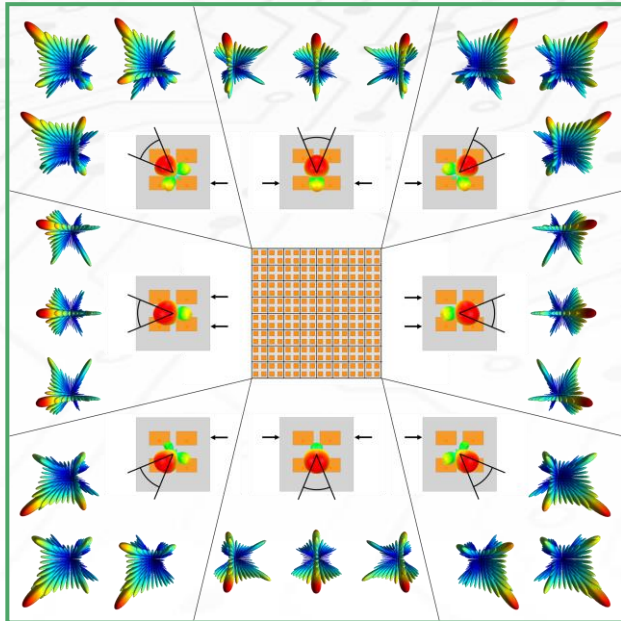
Smallest chiplet:  
10x10 μm



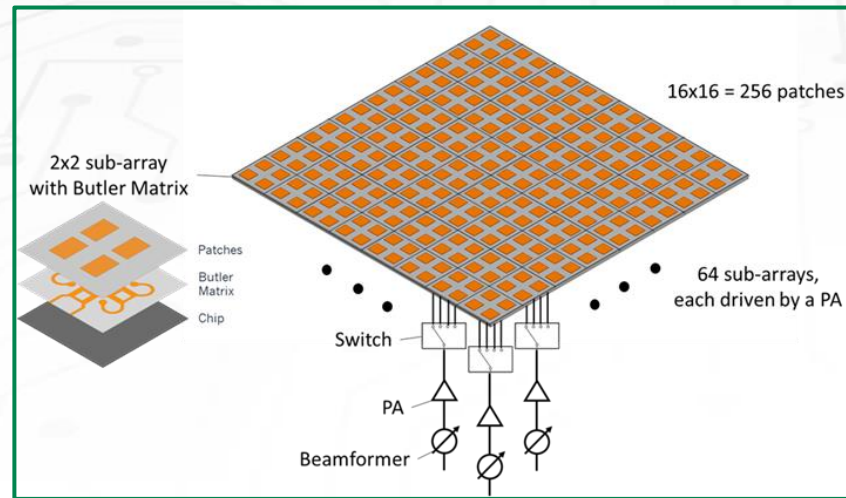
‘Sea of Chiplets’

# Addressing the Three Challenges: Technical Approach

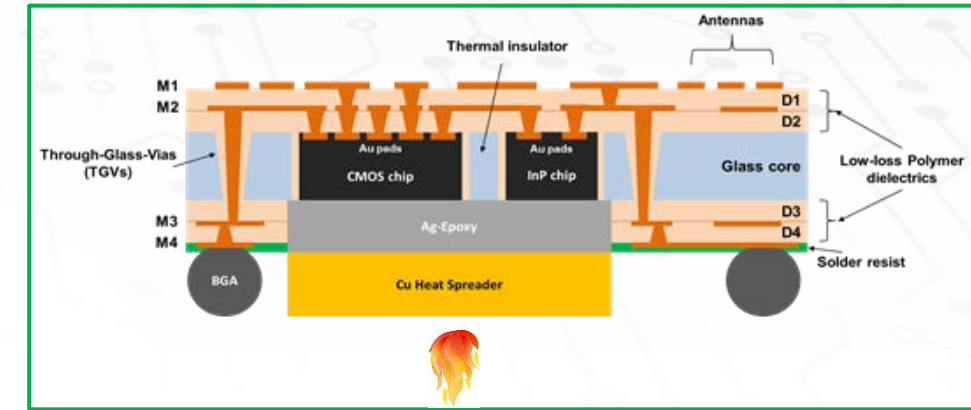
## Antenna in Package



## Minimizing Package Loss



## Heat Removal



### ❑ Antenna in Package

- Hybrid Beamforming Architecture
- Large 2D Array for Full Field of View (Tx)
- 2x2 Sub-Array
- 2D Butler Matrix
- 1D Array for Rx

### ❑ Minimizing Package Loss

- Embedded IC
- Eliminate assembly
- High frequency polymer layers
- Low loss interconnects
- Electronics beneath antenna

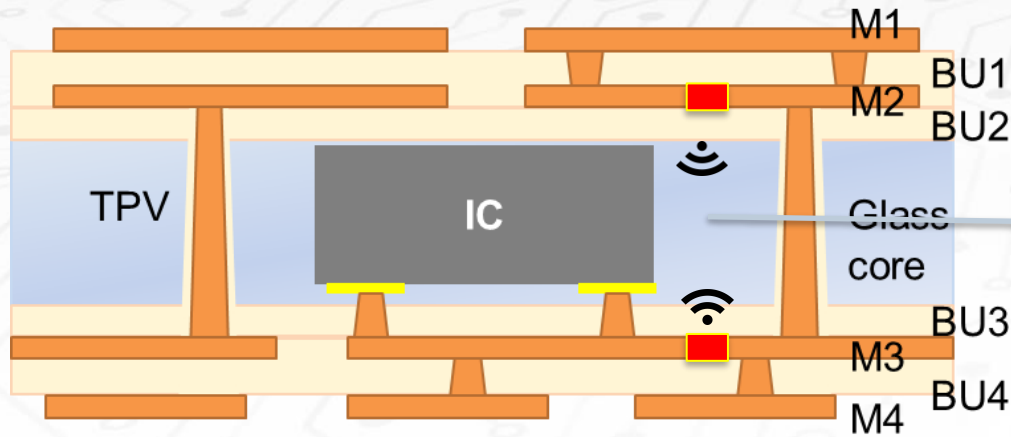
### ❑ Heat Removal

- Thru cavities in Glass
- Exposed IC
- Thermal Interface Material
- Heat Spreader
- Minimize thermal resistance

Outcome of SRC Workshop, Feb '20, Georgia Tech

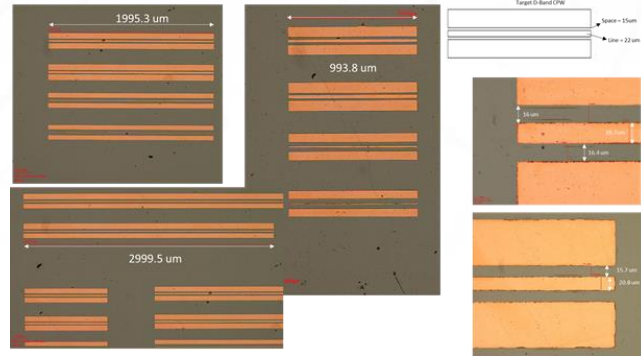


# D-Band Interconnects



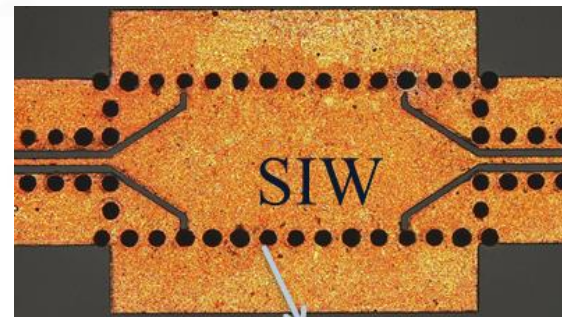
1. Co-planar Waveguide (CPW)
2. Microstrip (MS)
3. Substrate Integrated Waveguide (SIW)
4. Via-less Interconnect
5. Conductor Backed Dielectric Waveguide (CBDW)

CPW & MS



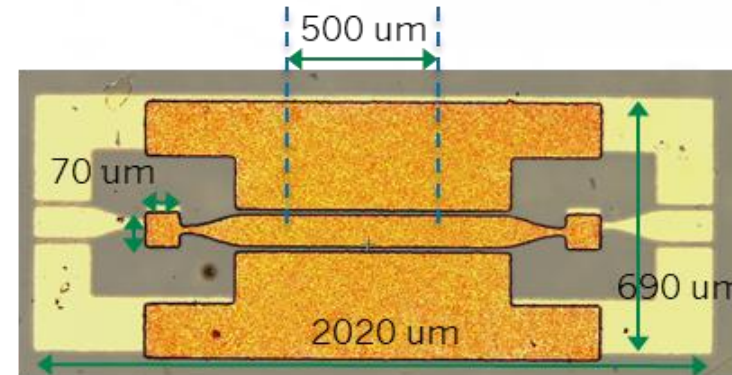
CPW Loss:  
0.25dB/mm  
MS Loss: 0.25dB/mm  
– 0.43dB/mm

SIW



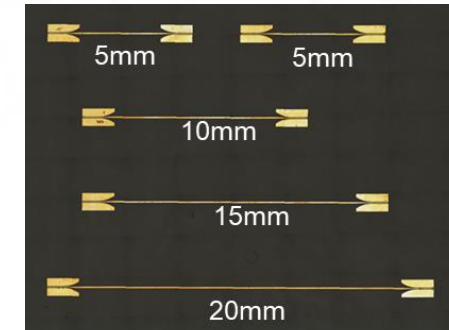
SIW Loss: 0.7dB/mm

Via-less



Via-less Loss: 1.8dB

CBDW



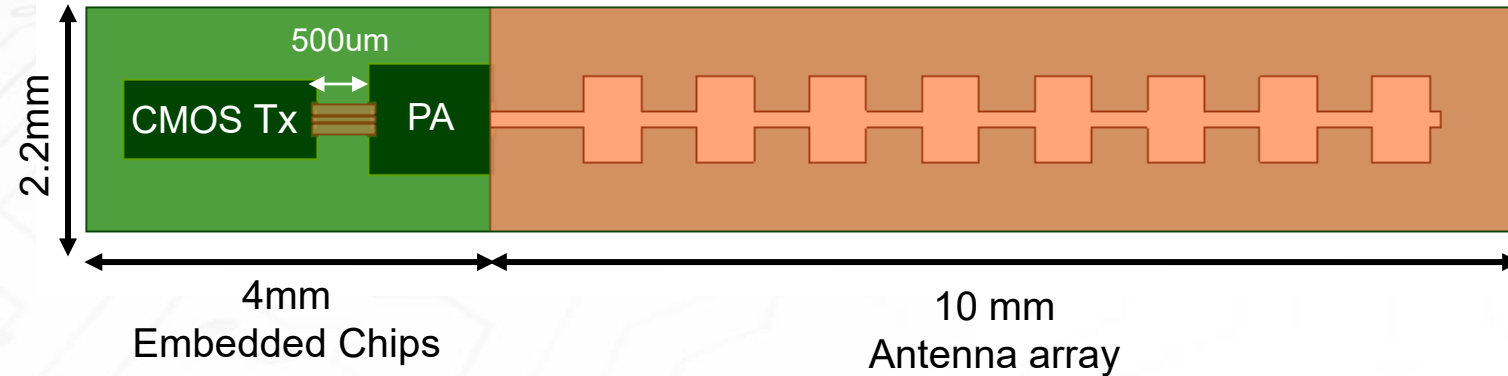
CBDW Loss:  
0.34dB/mm



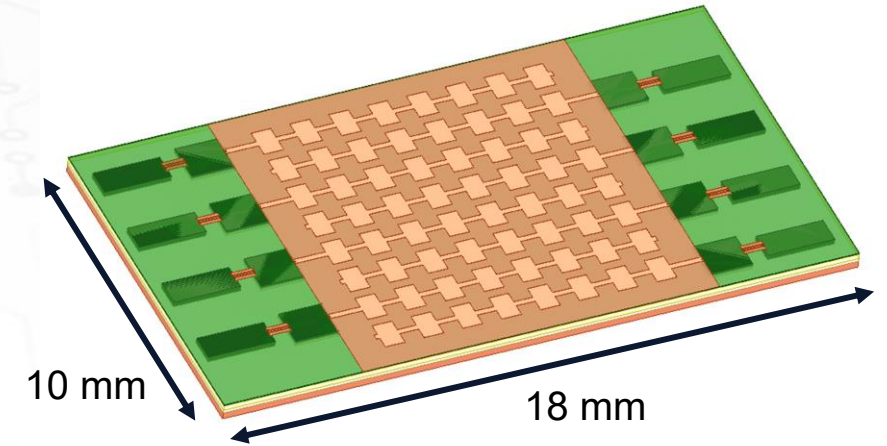
# 140GHz 8x8 Array Functional Module (w/ ComSenTer)

CMOS Tx 1.9mm \* 0.76mm \* 0.150mm  
InP PA 1.23mm \* 1.09mm \* 0.075mm

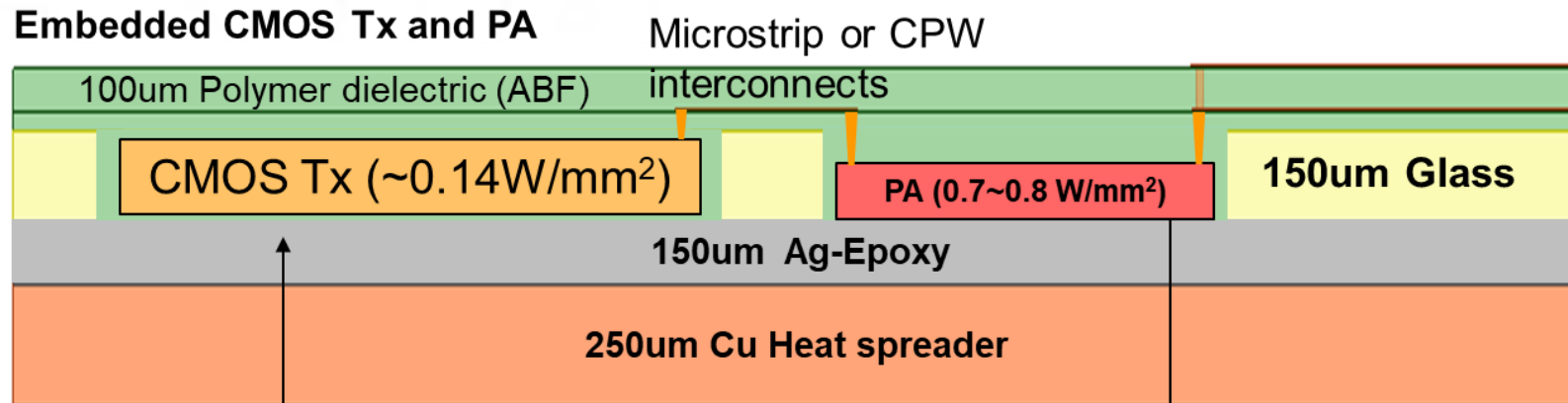
Top view of unit module



8x8 Antenna array module



## Cross-section of Embedded module



Antenna array is here  
→

CMOS chip is 150µm thick

InP PA is 75µm thick

Seismic Shift 5. Compute Energy vs. Global Energy Production, Task ID: 2778.044

# Thermally Enhanced Organic Substrates for GaN Power Amplifiers

*Student: Min Jong Kil, Sam Ellison*

*Faculty: Timothy S. Fisher – Mechanical and Aerospace Engineering, UCLA*

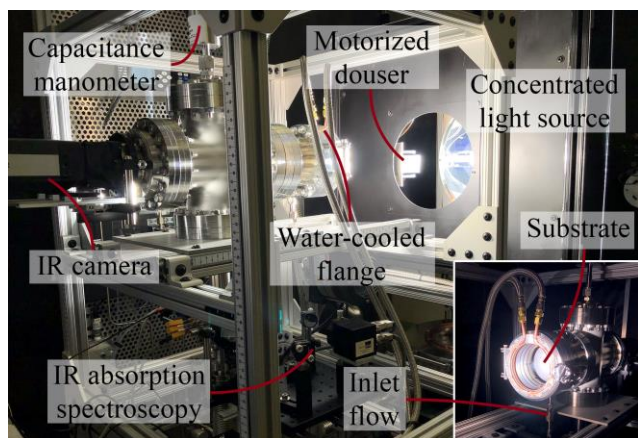
## Task Focus and Goal

- Improve heat removal capability of organic substrates in high-power GaN power amplifiers
- Enhance thermal management with a ten-fold reduction in heat spreading resistance

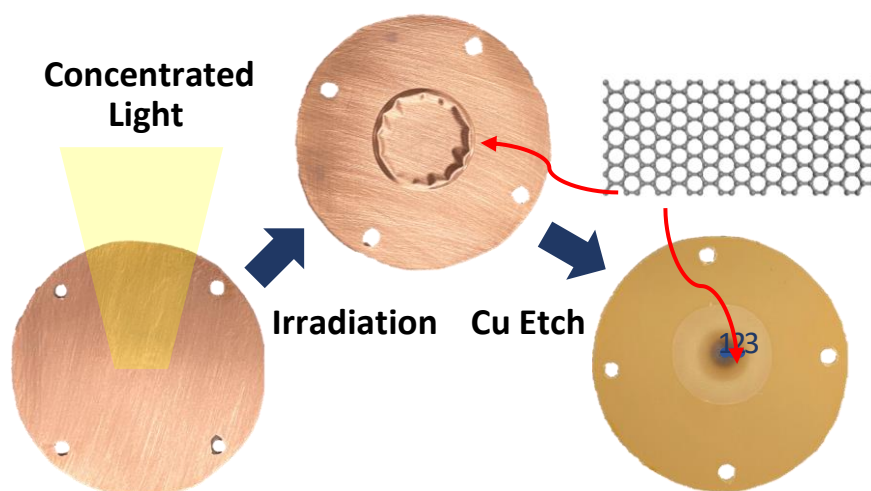
## Technical Approach

- Green manufacturing: 10 kW<sub>e</sub> concentrated simulated solar source with a maximum controllable peak flux of 4.5 MW/m<sup>2</sup>
- Epoxy is converted into graphitized layers by short-duration, high-flux irradiation in vacuum

## Overview

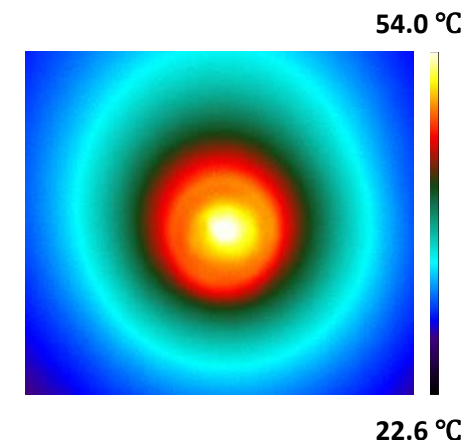
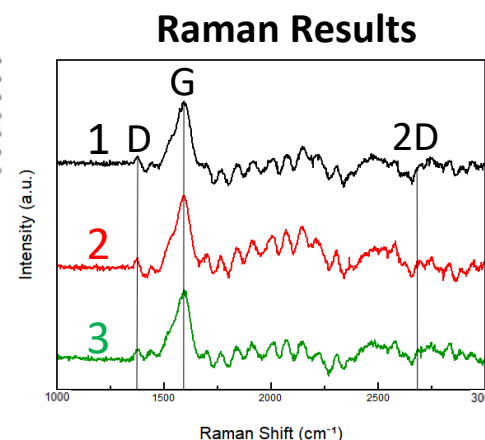


**Concentrated Light Source**

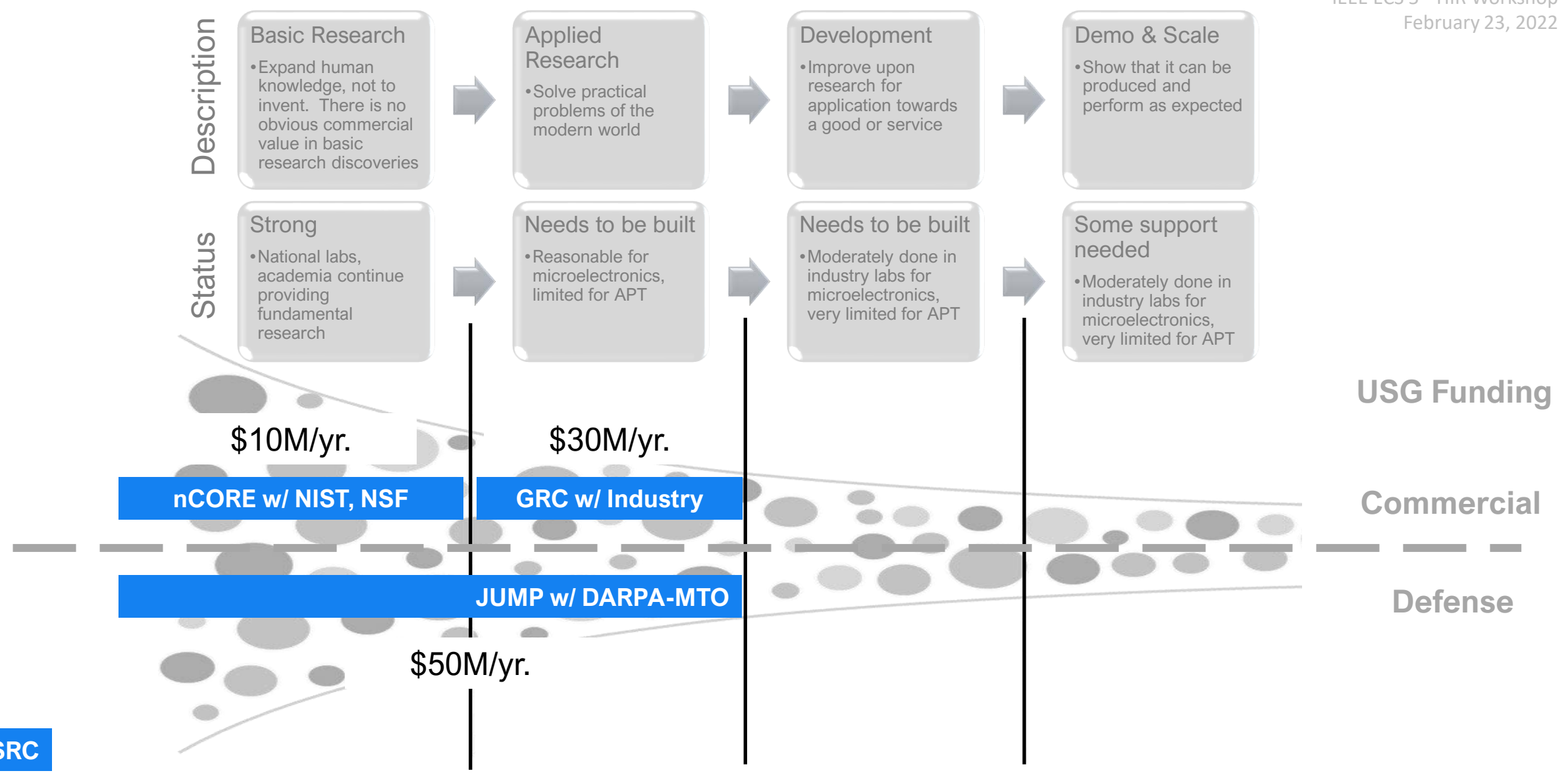


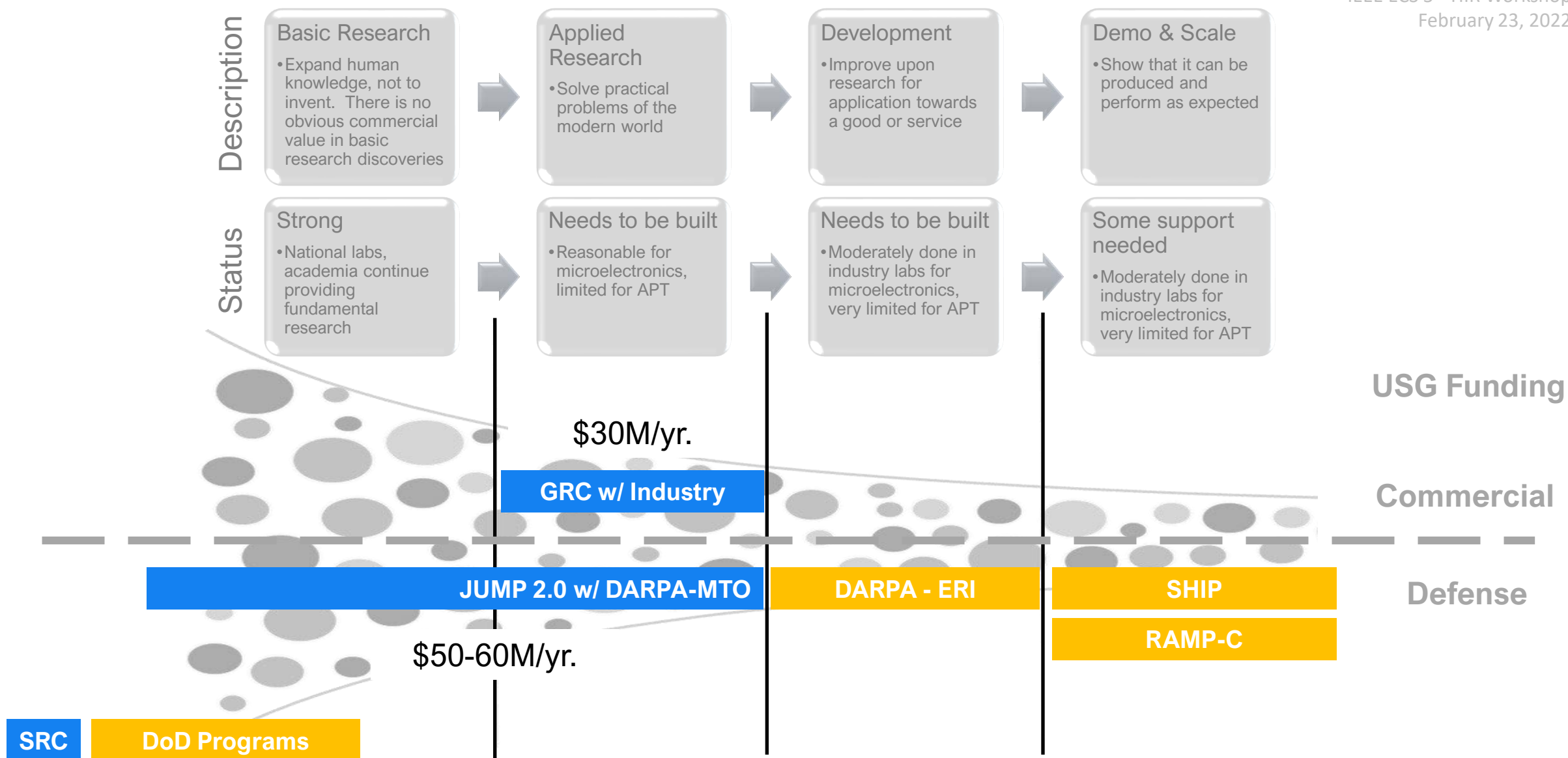
**ASTRA MT77  
(epoxy with Cu clad)**

**Centrally Graphitized Region**



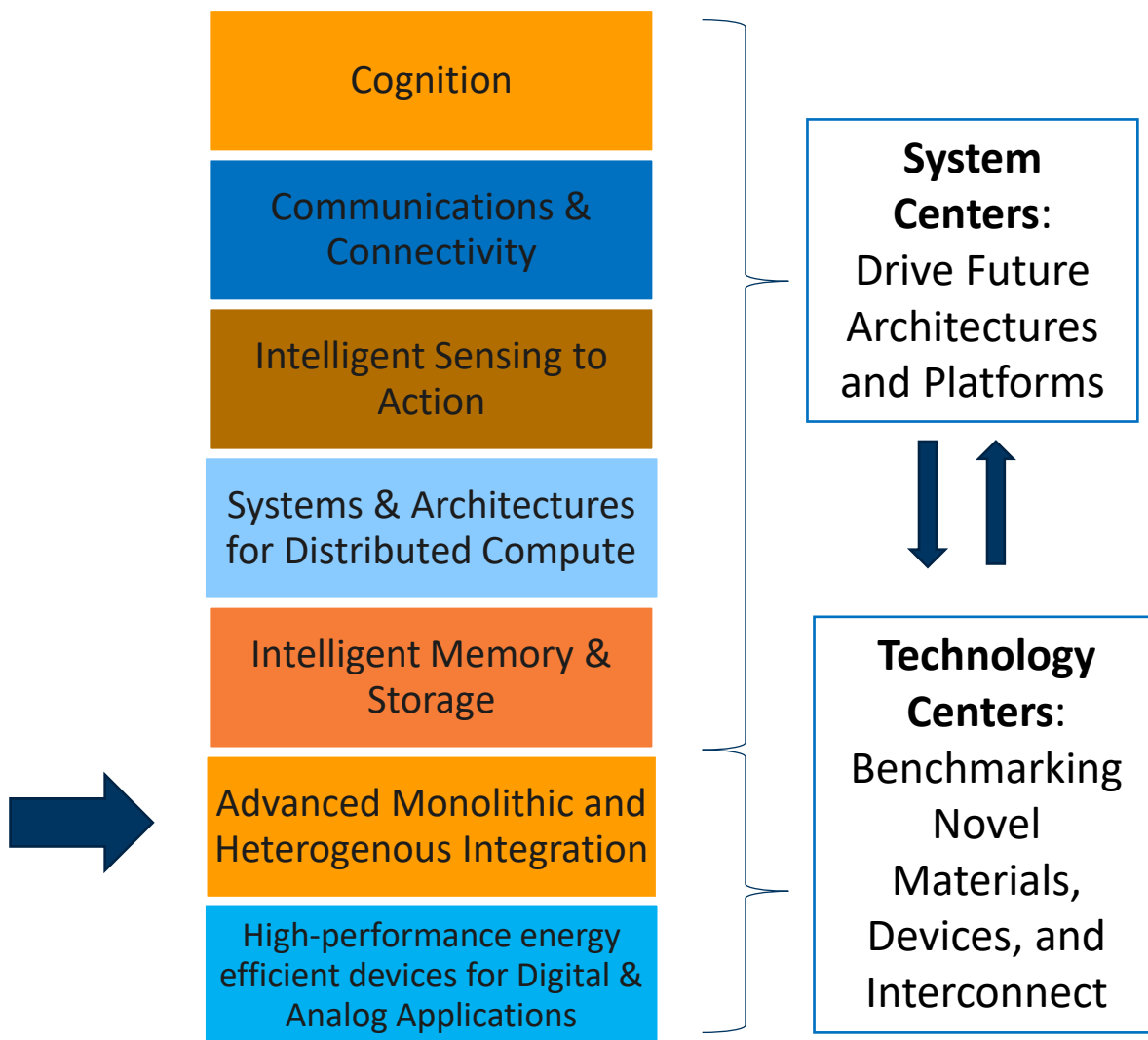
This work was supported in part by the Semiconductor Research Corporation (SRC) and DARPA.





Jan 2023+. Announced [JUMP 2.0 with DARPA](#). Center & individual whitepapers due March 7<sup>th</sup>, 2022.

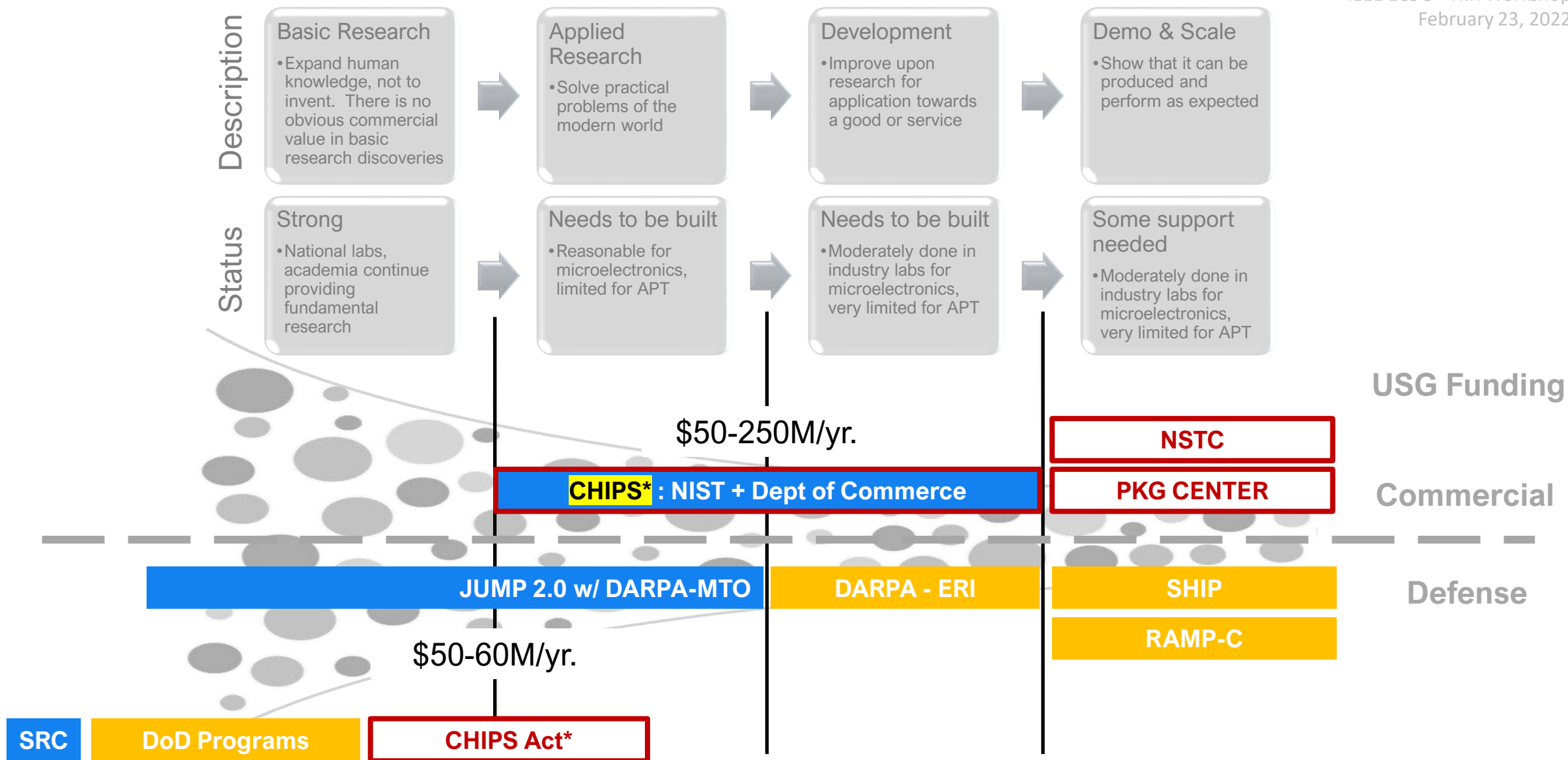
# JUMP 2.0 Focus Centers



- System Centers: what are the technology implications?
- Technology Centers: what are the architectural implications?
- Target budget per Center: \$5M-\$7M/yr.
- Right-size for Critical-mass & Critical Mind Share.
- Recommended:
  - ~20 PIs\*
  - Median task size: ~\$250k/yr.
- # of Universities not specified; find a balance. (See [FAQs](#), Q4)

\*NOTE: Do not submit whitepaper with full team. See solicitation.



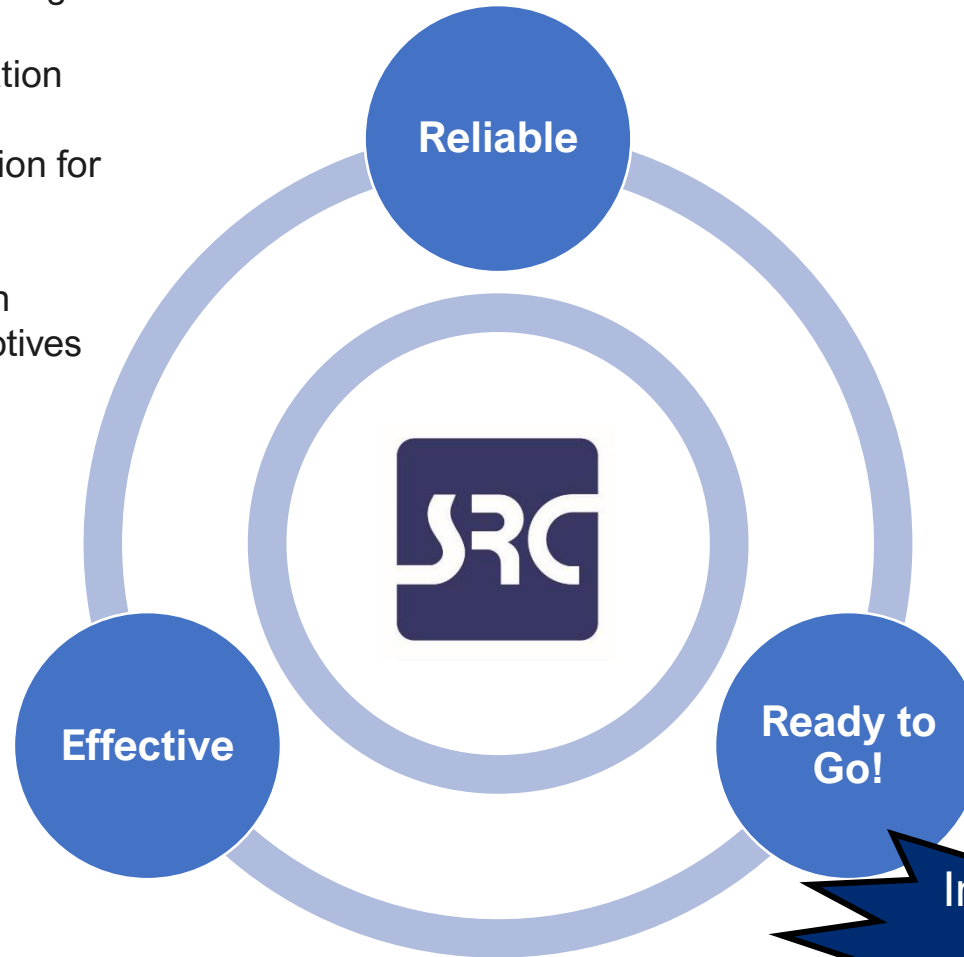


With anticipated CHIPS ACT funding; \*Congressional legislation pending



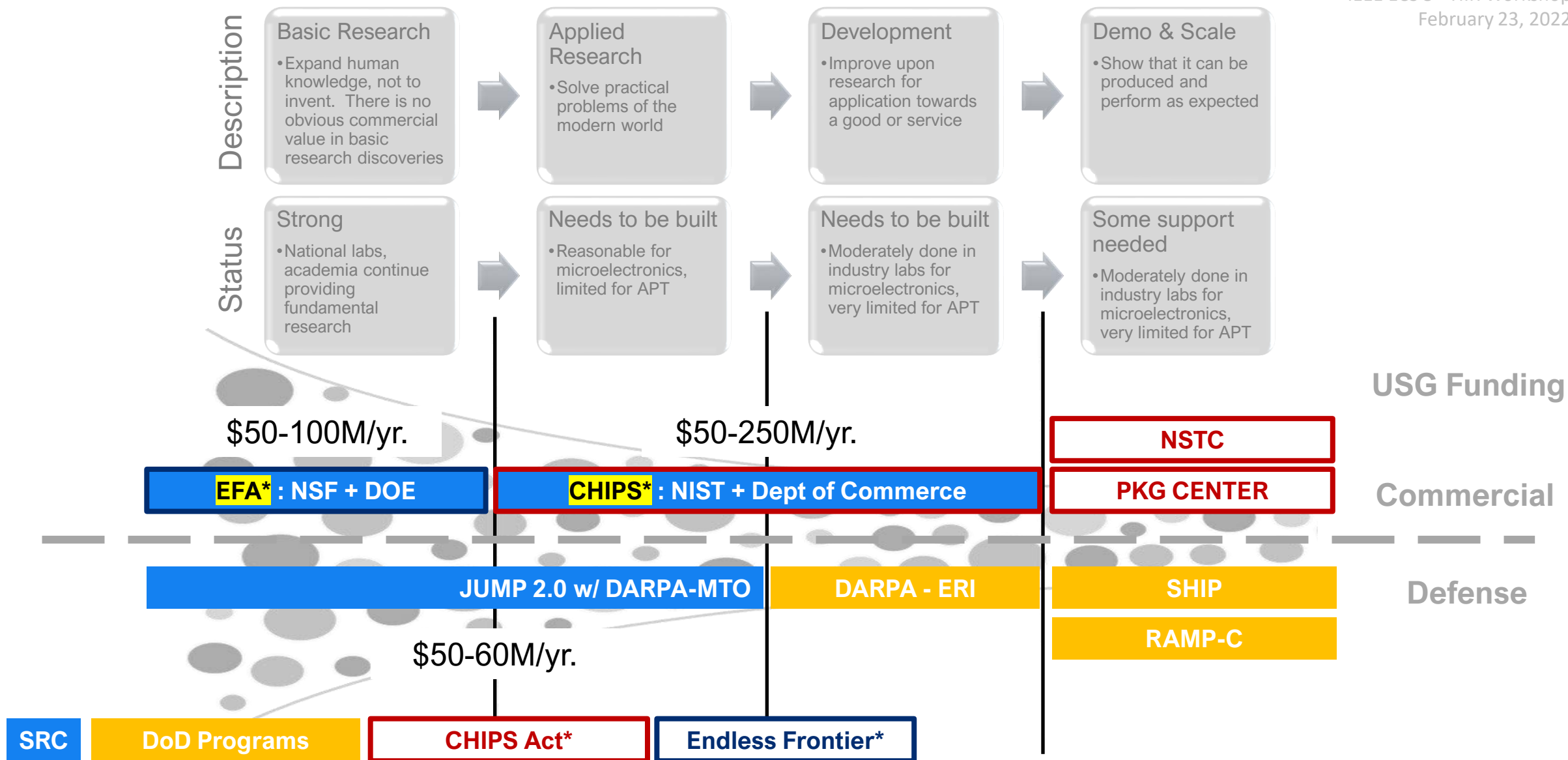
# Why SRC is the Right Organization to Lead

- Low risk. A 40-year history of working with companies, universities, and governments across many innovation programs
- Often sited as the go-to organization for Industry- Government- Academic collaboration
- A Non-profit, neutral 3<sup>rd</sup> party with nothing to gain and no ulterior motives or outside influences
- Bringing industry for effective technology transfer that benefits the university and the market
- Develop technology that's shaped the industry for 40 years
- Consistently builds communities where they are needed



- Membership contracts active with 26 industry members and 3 gov't agencies, research contracts active with 100+ universities
- Existing processes for defining meaningful research agenda that generates results and partnering with government
- In-house Technical Program Managers including Industrial Researchers, Contracting, Program Management, Billing, User portal, Legal, etc.

In 2021,  
\$90M



Ideal Build Out; \*Congressional legislation pending

# Future Talent



Drive holistic, optimal solutions in HW/SW through interlocked multidisciplinary research

Help students see we have hard yet interesting problems that can't be solved without them

Convey to students that opportunities are abound for the next 20-30 years

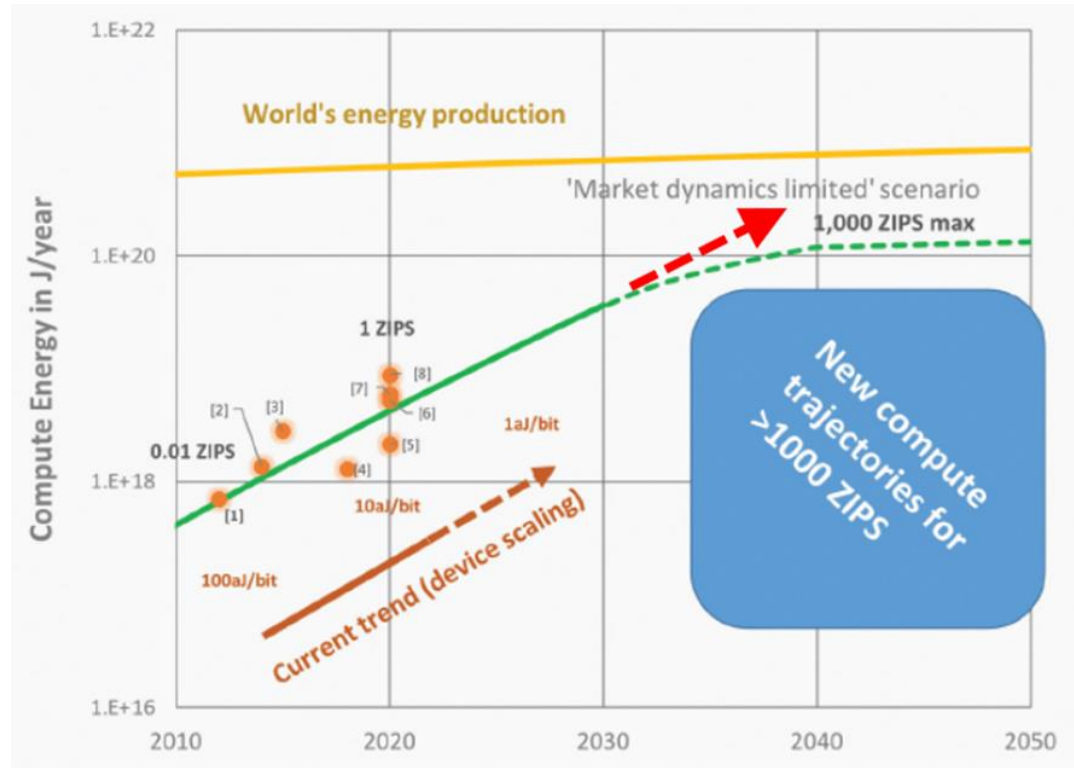
Create industrial relationships and internship experiences that provide insight into SOTA\*

\*SOTA = State of the Art

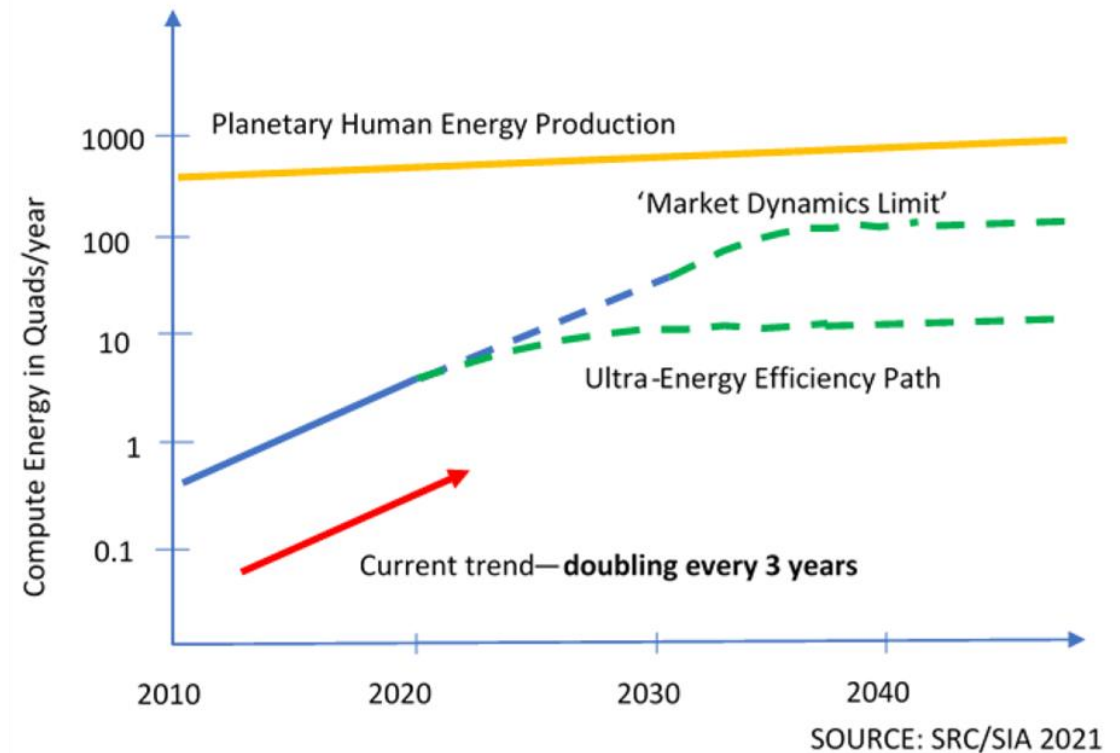
**We need an aspirational new narrative that ignites the next generation of talent**

# Compute Energy vs. Global Energy Production

Seismic Shift #5



2030 Decadal Plan for Semiconductors



DOE-AMO Workshop, Apr 21-23, 2021

This is not only critical for our society and planet, but sustainable microelectronics **can win the hearts & minds of young innovators.**

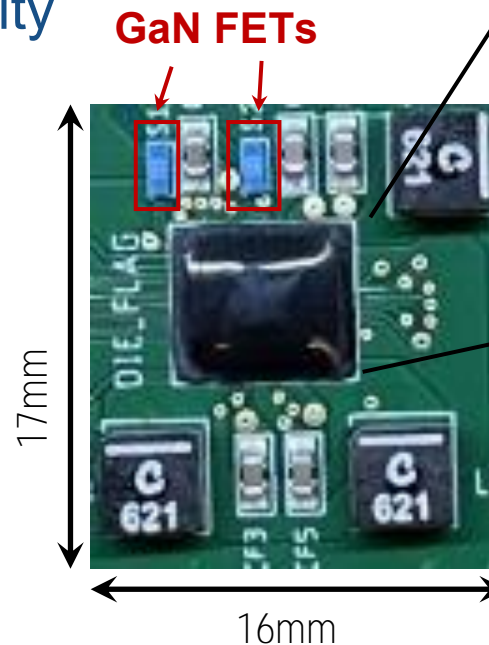


# High Voltage DC-DC Converter with Package- and Board-level GaN/Si Integration

- Optimized design with high-performance low-voltage Si devices with high-voltage GaN devices
- Breakthrough efficiencies for 48V-to-1V and 24V-to-1V conversions.
- Compact design for high energy-density

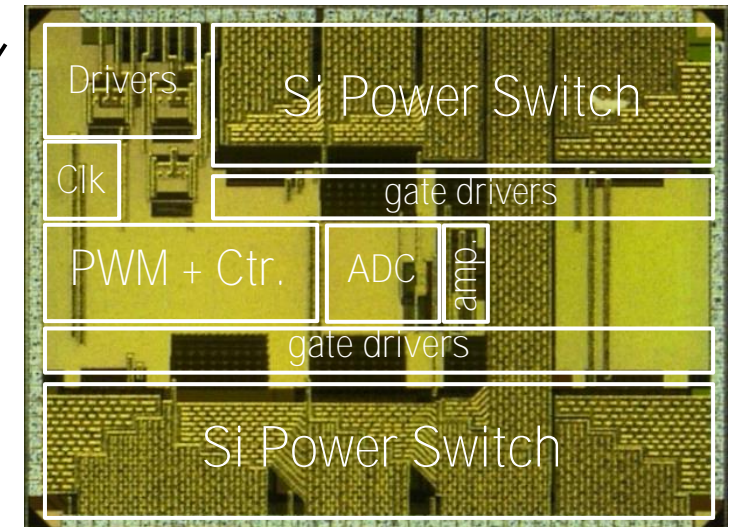
<b>Topology</b>	3-level hybrid Dickson
<b>Area</b>	16mm x 17mm
<b>Input Voltage</b>	48V
<b>Output Voltage</b>	0.7-1V
<b>GaN FETs</b>	Enhanced mode GaN
<b>Inductor</b>	3 x 0.62uH
<b>Peak Efficiency</b>	90.4%@48-1V, 1MHz
<b>Current Density</b>	240/ *955A/inch <sup>3</sup>

\*Component area only  
Latest Prototype



Converter Board

## Die shot and characters



<b>Technology</b>	180nm HV BCD
<b>Area</b>	4mm x 3mm
<b>Si Switch</b>	24V/20V/16V/12V/6V N-type LDMOS
<b>V<sub>DD</sub></b>	5V

# Call to Action

- The ICT opportunities of tomorrow are simply **unachievable with emerging hardware technologies** as the underlying hardware is up against fundamental physical limits.
- A crisis is at hand, where the hardware paradigm must shift to create the desired value with **3D microelectronic** and **advanced packaging technologies (MAPT) as the key driver**.
- To stay at the leading edge of hardware innovation, we must invest in early-stage ideas and tech maturation, exploring options through a **fast-fail** and **tech-transfer mindset**.
- It is equally important that we are **committed to workforce development** and **broadening participation**.
- We must seek and create **energy efficient systems** via **eco-considerate manufacturing**.
- There is a bright future for semiconductors, but we must change our own narratives to win over the hearts and minds of next gen innovators.

***Investment in Heterogeneous Integration is priority #1. We must act, now!***



# SRC's Mission For The Roaring 20s



Semiconductor Technology Leadership

- [2030 Decadal Plan for Semiconductors](#)

Diverse Student Pipeline

- [Broadening Participation Pledge](#)

Eco-Considerate Processes and Systems

- [Commitment to Sustainability](#)

Learn more at <https://www.src.org/about/>